

RJK6014DPP

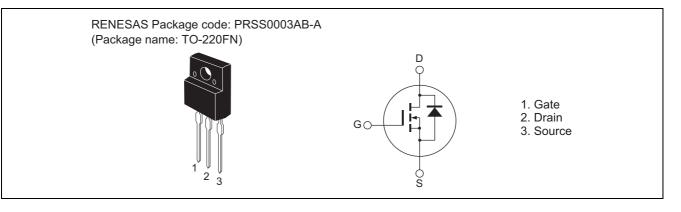
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1531-0100 Rev.1.00 Apr 17, 2007

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	(1a = 25 C) Unit
Drain to source voltage	V _{DSS}	600	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	ID ^{Note4}	16	А
Drain peak current	I _{D (pulse)} Note1	32	А
Body-drain diode reverse drain current	I _{DR}	16	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	32	А
Avalanche current	I _{AP} ^{Note3}	4	А
Avalanche energy	E _{AR} ^{Note3}	0.87	mJ
Channel dissipation	Pch ^{Note2}	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

2. Value at Tc = $25^{\circ}C$

3. STch = 25°C, Tch $\leq 150^{\circ}C$

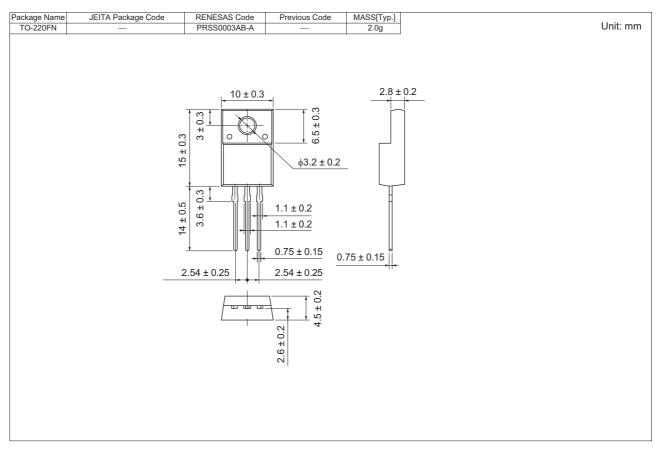
4. Limited by maximum safe operation area

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600	_	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.475	0.575	Ω	$I_D = 8 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss		1800		pF	V _{DS} = 25 V
Output capacitance	Coss	_	170	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	20	_	pF	
Turn-on delay time	t _{d(on)}	_	36	—	ns	I _D = 8 A
Rise time	tr	_	29	—	ns	$V_{GS} = 10 V R_L = 37.5 \Omega Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	93	—	ns	
Fall time	t _f	_	20	—	ns	
Total gate charge	Qg	_	45	—	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	9	—	nC	V _{GS} = 10 V I _D = 16 A
Gate to drain charge	Qgd	_	20	—	nC	
Body-drain diode forward voltage	V _{DF}	_	0.91	1.50	V	$I_F = 16 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}	_	390	—	ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK6014DPP-00-T2	1050 pcs	Box (Tube)

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